1SS133

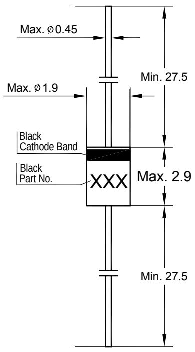
Silicon Epitaxial Planar Switching Diode

Features

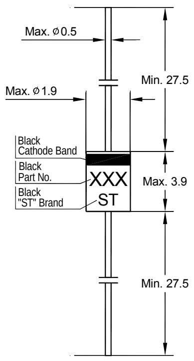
- Glass sealed envelope
- High speed
- High reliability

Applications

- High-speed switching



Glass Case DO-34
Dimensions in mm



Glass Case DO-35
Dimensions in mm

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V_{RM}	90	V
DC Reverse Voltage	V_R	80	V
Average Rectified Forward Current	$I_{F(AV)}$	130	mA
Peak Forward Current	I_{FM}	400	mA
Surge Forward Current at t < 1 s	I_{FSM}	600	mA
Power Dissipation	P_{tot}	300	mW
Junction Temperature	T_j	175	°C
Storage Temperature Range	T_{stg}	- 65 to + 175	°C

Characteristics at T_a = 25 °C

Parameter	Symbol	Max.	Unit
Forward Voltage at I_F = 100 mA	V_F	1.2	V
Reverse Current at V_R = 80 V	I_R	0.5	µA
Capacitance between Terminals at V_R = 0.5 V, f = 1 MHz	C_T	2	pF
Reverse Recovery Time at I_F = 10 mA, V_R = 6 V, R_L = 50 Ω	t_{rr}	4	ns

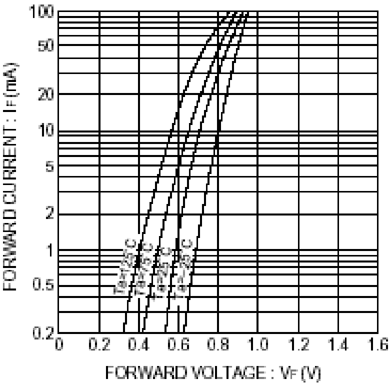


Fig. 1 Forward characteristics

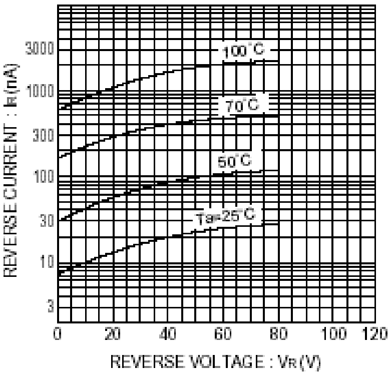


Fig. 2 Reverse characteristics

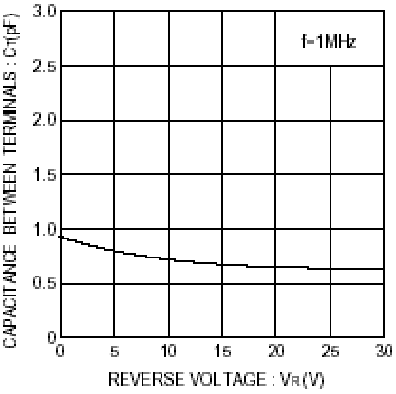


Fig. 3 Capacitance between terminals characteristics

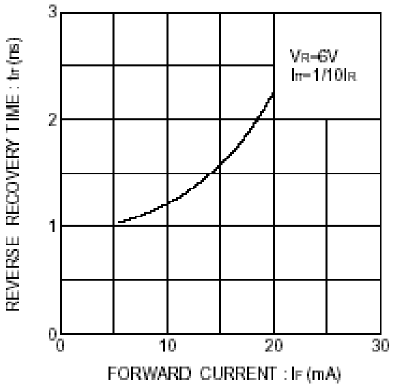


Fig. 4 Reverse recovery time characteristics

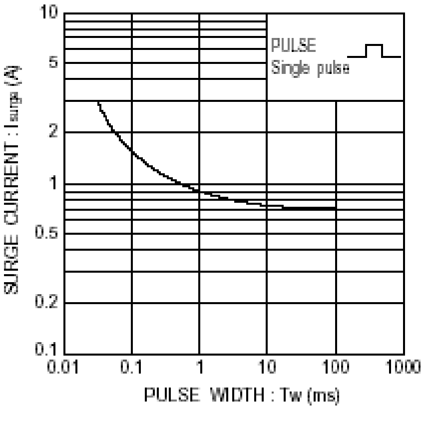


Fig.5 Surge current characteristics

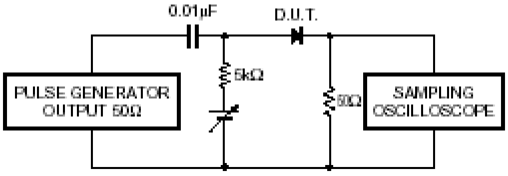


Fig. 6 Reverse recovery time (trr) measurement circuit